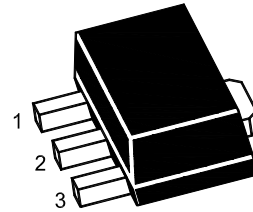


Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURE

- Switching and amplification in high voltage
Applications such as telephony
- Low current(max. 500mA)
- High voltage(max.160v)



1.Base 2.Collector 3.Emitter
SOT-89 Plastic Package

MARKING:5401

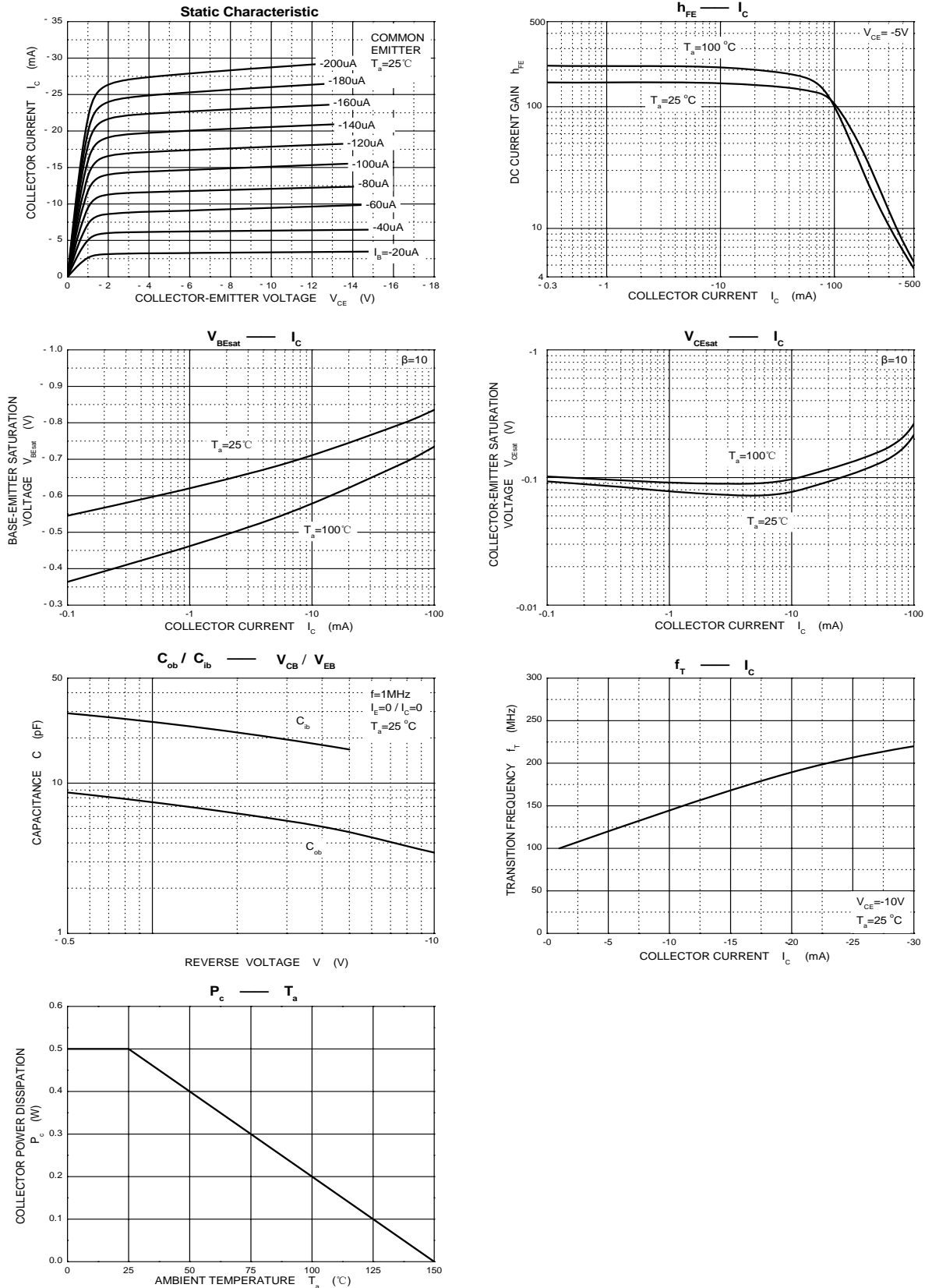
MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-160	V
V _{CEO}	Collector-Emitter Voltage	-150	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.5	A
P _C	Collector Power Dissipation	0.5	W
R _{θJA}	Thermal Resistance From Junction To Ambient	250	°C/W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C

ELECTRICAL CHARACTERISTICS(T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100μA, I _E =0	-160			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -1mA, I _B =0	-150			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -10μA, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} = -120 V, I _E =0			-50	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -3V, I _C =0			-50	nA
DC current gain	h _{FE(1)}	V _{CE} = -5V, I _C =-1 mA	50			
	h _{FE(2)}	V _{CE} = -5V, I _C = -10 mA	60		300	
	h _{FE(3)}	V _{CE} = -5V, I _C =-50 mA	50			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -10 mA, I _B = -1 mA			-0.2	V
	V _{CE(sat)}	I _C = -50 mA, I _B = -5 mA			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -10 mA, I _B = -1 mA			-1	V
	V _{BE(sat)}	I _C = -50 mA, I _B = -5 mA			-1	V
Transition frequency	f _T	V _{CE} = -10V, I _C = -10mA, f = 100MHz	100		300	MHz
Output Capacitance	C _{ob}	V _{CB} =-10V, I _E = 0,f=1MHz			6	pF
Noise Figure	NF	V _{CE} = -5.0V, I _C = -200μA, R _S = 10Ω,f =10Hz to15.7kHz			8	dB

Typical Characteristics





CHINA BASE
INTERNATIONAL

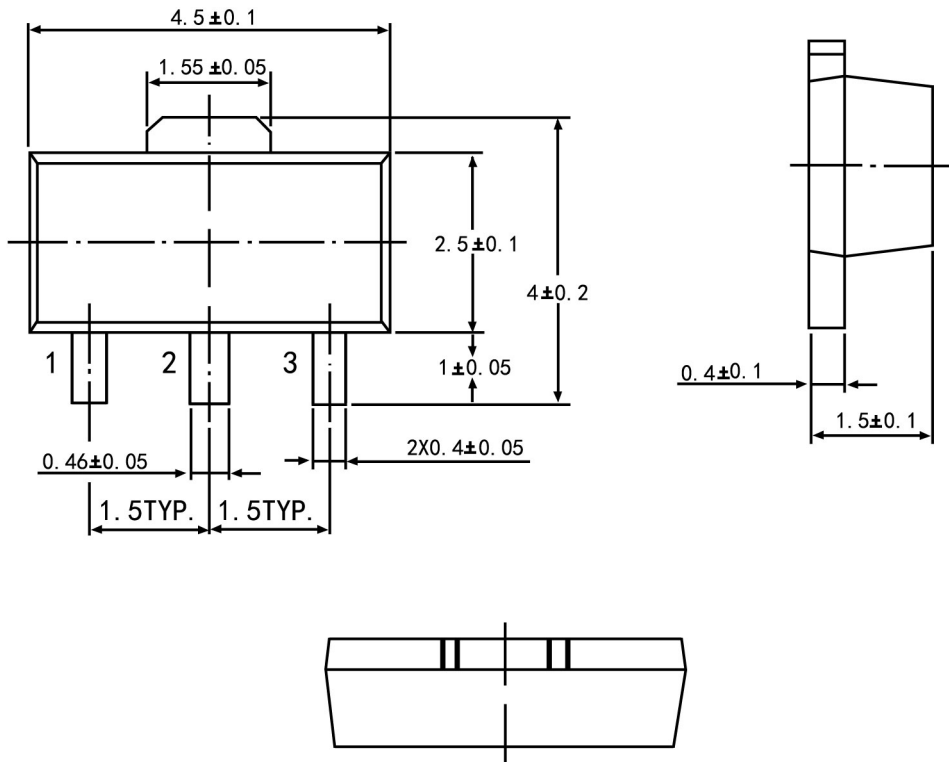
SOT-89

2N5401U



www.china-base.com.hk

SOT-89 PACKAGE OUTLINE



Symbol	Dimension in Millimeters	
	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
All Dimensions In mm		

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Bipolar Transistors - BJT category](#):

Click to view products by [Hong Kong Chuangji manufacturer](#):

Other Similar products are found below :

[BC559C](#) [MCH4017-TL-H](#) [MMBT-2369-TR](#) [BC546/116](#) [NJVMJD148T4G](#) [NTE16](#) [NTE195A](#) [IMX9T110](#) [2N4401-A](#) [2N6728](#) [2SA1419T-TD-H](#) [2SA2126-E](#) [2SB1204S-TL-E](#) [FMC5AT148](#) [2N2369ADCSM](#) [2N2907A](#) [2N3904-NS](#) [2N5769](#) [2SC4618TLN](#) [CPH6501-TL-E](#) [MCH4021-TL-E](#) [US6T6TR](#) [BAX18/A52R](#) [BC556/112](#) [IMZ2AT108](#) [MMST8098T146](#) [UMX21NTR](#) [MCH6102-TL-E](#) [TTA1452B,S4X\(S](#) [2N3879](#) [NTE13](#) [NTE282](#) [NTE323](#) [NTE350](#) [NTE81](#) [JANTX2N2920L](#) [JANTX2N3735](#) [JANSR2N2222AUB](#) [CMLT3946EG TR](#) [SNSS40600CF8T1G](#) [2N6987](#) [CMLT3906EG TR](#) [GRP-DATA-JANS2N2907AUB](#) [GRP-DATA-JANS2N2222AUA](#) [MMDT3946FL3-7](#) [2N4240](#) [JANS2N3019](#) [MSB30KH-13](#) [2N2221AUB](#) [2SD1815T-TL-E](#)